Evaluation of grain boundaries as percolation pathways in quartz-rich continental crust using Atomic Force Microscopy

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S1: SUPPLEMENTARY FIGURE S1

Schematic regional map showing the locations of and contacts between the Singhbhum Craton, Rengali Province and Eastern Ghats Mobile Belt drawn using Corel Draw X5.

S2. Width of Grain Boundaries for each sample

Table R1: Grain Boundary Width Measurements (Average width values mentioned in **bold**, Standard deviation values mentioned in red)

| 577 | | | |
|------------|--|--|--|
| 603 | | | |
| 513 | | | |
| 540 | | | |
| 580 | | | |
| 323.197530 | | | |
| u | | | |
| 81.5506234 | | | |
| | | | |

S3. Determination of Plastic Deformation from FD curves:

Figure S2. FD curve for location 5 (area 2) of ANG 1, showing determination of plastic deformation. Inset figure shows the magnified version of the encircled region of the FD curve.

Zero-load plastic deformation (ΔZ) is determined by the difference in the value of Z of approach curve and the tangent to the retraction curve which meets at zero deflection (or zero force, $y = 0$), shown in Figure S2 for sample ANG 1 (location 5, area 2), as previously reported by Cappella et.al.¹ Zero load plastic deformation data obtained at all locations for both samples (ANG 1 and RN 171) are listed below in table R2 and R3.

Table R2: Plastic Deformation Data for sample ANG 1 calculated at different locations for three different areas. The **i**mages have been generated using PicoImage Basic Rendering Software (produced by Digital Surf), that comes integrated with Agilent PicoView Software (Version 1.14.4, Agilent Technologies) URL: [https://www.keysight.com/in/en/lib/software](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html)[detail/instrument-firmware-software/for-your-convenience-you-can-now-download](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html)[picoview-and-pico-image-software-for-your-afm-2282256.html.](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html) Further, for better visual clarity, the numbers and the line profiles were drawn using MS Paint.

Table R3: Plastic Deformation Data for sample RN 171 calculated at different locations for two different areas. The **i**mages have been generated using PicoImage Basic Rendering Software (produced by Digital Surf), that comes integrated with Agilent PicoView Software (Version 1.14.4, Agilent Technologies) URL: [https://www.keysight.com/in/en/lib/software](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html)[detail/instrument-firmware-software/for-your-convenience-you-can-now-download](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html)[picoview-and-pico-image-software-for-your-afm-2282256.html.](https://www.keysight.com/in/en/lib/software-detail/instrument-firmware-software/for-your-convenience-you-can-now-download-picoview-and-pico-image-software-for-your-afm-2282256.html) Further, for better visual clarity, the numbers and the line profiles were drawn using MS Paint.

S4. Calculation of applied force (P) using Hooke's Law:

To determine the applied force (P) , the following tip properties are required:

Deflection sensitivity, **A** (as extracted from PicoView Spectroscopy software using rigid known sample) = 15 nm/V

Tip Force Constant, **k** (as provided by the manufacturer of AFM tips) = 48 N/m

Now, vertical tip deflection, δ can be related to electrical signal (generated in photodiode in volts): 2°

δ ² = *A* (*D - D₀*)**……….**(1)

D is considered as the maximum deflection signal on FD curve (See figure S3) and **D⁰** is the initial signal. From the FD curve, we obtain $D = 10.0$ V and $D_0 = 0.5$ V and using $A = 15$ nm/V in equation 1, we obtain δ **= 142.5 nm**.

Further, δ can be utilized to calculate the applied force, P on the tip, which is typically modelled as a spring obeying Hooke's Law.^{1, 2} Thus, force on the AFM tip can be related as, *P* $= k \delta$ **….** (2) (where **k** = tip force constant in N/m). Using the values of **k** and δ as mentioned above in equation 2, we get $P = 6840$ nN or 6.84 μ N.

S5. Determination of Elastic Modulus:

Figure S3. Representative distance vs deflection curve generated for rigid Silicon substrate (known sample).

Determination of elastic modulus of an unknown sample requires certain parameters that are inherent to the material and make of the tip. Deflection sensitivity (**A**) and cantilever-tip property (**α**) are determined from the PicoView software using a rigid sample (Silicon Wafer Substrate) as known sample and by calculating from the following equations:^{2, 3}

$$
\frac{1}{E_r} = \frac{(1 - \theta_i)^2}{E_i} + \frac{(1 - \theta_s)^2}{E_s} \dots (3)
$$

\n
$$
|K| = A \left(1 + \frac{k}{2E_{r} a} \right) \dots (4)
$$

\n
$$
\alpha = \frac{k}{2.a} \dots (5)
$$

\n
$$
E_{r=1} \frac{a}{\frac{|K|}{A} 1} \dots (6)
$$

Where: E_s , E_i and E_r = elastic modulus of sample, indenter (AFM tip) and reduced elastic modulus respectively, in Pascal. θ_i , θ_s = Poisson's Ratio of Indenter and Sample respectively. $K = 1$ / slope of retraction curve (nm/V), $A =$ deflection sensitivity (nm/V), $k =$ tip force constant (N/m), \mathbf{a} = contact radius (nm), $\boldsymbol{\alpha}$ = cantilever tip property in Pa.

Taking the values of $E_s = 112.40$ GPa and $\vartheta_s = 0.28$ for known sample (Si Wafer substrate) from published literature^{4,5} and the values of $E_i = 310$ GPa and $\theta_i = 0.27$ for silicon nitride AFM tip,⁶ we find $E_r = 0.1579 \times 10^{-12}$ Pa. This value of E_r is used to find *a* from equation 4, where $|\mathbf{K}| = 16$ nm/V for Si substrate (determined from the FD retraction curve for Si substrate, See Figure S3). With the calculated value of *a* which is 2278.78 x 10^{-12} nm, we then find α from equation 5, which is calculated to be ≈ 10.5 GPa.

Figure S4. Representative distance vs deflection curve generated for (**Series A**) ANG 1; (**Series B**) RN 171

Further to determine *Es* of the samples (ANG 1 and RN 171), we have obtained E_r (from eq. 6) using the values of $\alpha = 10.5$ GPa and $A = 15$ nm/V and *K*. The values of *K* have been determined from the average slope of the retraction curves generated for locations within grain boundaries and near the grain boundary of each sample (See figure S4). The value of *Er*, obtained, was used to calculate *Es* from equation 3, using the known values of E_i , ϑ_i , as mentioned above and $\mathbf{\vartheta}_{s} \approx 0.107$ from literature⁷.

Table R4: K-values (nm/V) for each location of sample ANG 1:

| Location | Area 1 | Area 2 | Area 3 |
|----------------|---------|---------|---------|
| | -14.9 | -14.9 | -14.6 |
| $\overline{2}$ | -16.5 | -16.1 | -15.2 |
| 3 | -15.7 | -15.2 | -14.9 |
| $\overline{4}$ | -15.2 | -14.9 | -14.9 |
| 5 | -14.9 | -14.6 | -15.6 |
| 6 | -14.6 | -16.7 | -15.6 |
| 7 | -16.7 | -16.7 | -15.2 |
| 8 | -16.1 | -14.8 | -16.7 |
| 9 | -17.1 | -17.1 | -14.6 |

As an example, below we show the calculation for obtaining elastic modulus (*Es*) of location within the grain boundary of ANG 1:

From table R4, $|K|_{avg}$ value for location within the grain boundaries (considering all three areas of the sample, for example: location 2, 10, 13 of area 1) is calculated to be \approx **15.75 nm/V** and $|K|_{avg}$ for locations surrounding the grain boundary (example: locations 1, 4, 7, 10 of area 1) is found to be ≈ 15.85 **nm/V**

Using α = 10.5 GPa (as calculated above), $|K|_{avg}$ = 15.75 nm/V in equation 6

$$
E_r = \frac{10.5}{\frac{15.77}{15} - 1}
$$

 $\Rightarrow E_r = 204.54 \text{ GPa}$ (within grain)

For location surrounding grain boundaries $|K|_{avg} = 15.85$ nm/V (See Table R4)

$$
E_r = \frac{10.5}{\frac{15.85}{15} - 1}
$$

 $\Rightarrow E_r = 185.29$ GPa (near grain boundaries)

Using $E_r = 204.54$ GPa and 185.29 in equation 3 we get,

$$
\frac{1}{204.54} = \frac{(1 - 0.27)^2}{310} + \frac{(1 - 0.107)^2}{E_s}
$$

 \Rightarrow $E_s = 252.2$ GPa (within grain)

and,

$$
\frac{1}{185.29} = \frac{(1 - 0.27)^2}{310} + \frac{(1 - 0.107)^2}{E_s}
$$

 \Rightarrow $E_s = 216 \text{ GPa}$ (near grain boundaries)

Table R5. K-values (nm/V) obtained from retraction curves for sample RN 171

| 1 | -17.8 | -16.2 |
|----------------|---------|---------|
| $\overline{2}$ | -15.7 | -16.2 |
| 3 | -16.8 | -17.1 |
| 4 | -15.7 | -15.7 |
| 5 | -15.7 | -16.8 |
| 6 | -15.7 | -15.7 |
| 7 | -16.7 | -17.3 |
| 8 | -17.1 | -17.1 |
| 9 | -17.1 | -17.3 |
| 10 | -16.2 | |
| 11 | -17.1 | |
| 12 | -16.2 | |

For RN 171, using the same method for calculation of elastic modulus (*Es*), as shown above, we get E_s (within grain) = 93.9 GPa and E_s (surrounding grain boundaries) = **113.21 GPa.**

References:

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